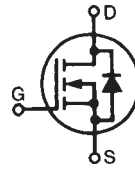


**Polar™ HiPerFET™  
Power MOSFET**
**IXFL32N120P**

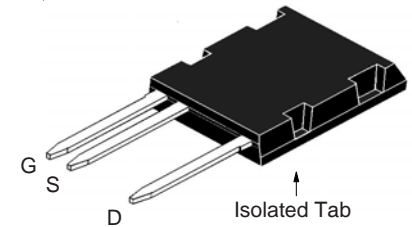
( Electrically Isolated Tab )

 N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode


$$\begin{aligned}
 V_{DSS} &= 1200V \\
 I_{D25} &= 24A \\
 R_{DS(on)} &\leq 340m\Omega \\
 t_{rr} &\leq 300ns
 \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1200	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$	1200	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	24	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$	100	A
$I_A$	$T_C = 25^\circ\text{C}$	16	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	2	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$	20	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	520	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS, 1 minute	2500	V~
	$I_{ISOL} \leq 1\text{mA}$ $t = 1\text{s}$	3000	V~
$F_C$	Mounting Force	40..120/4.5..27	N/lb.
<b>Weight</b>		8	g

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 3\text{mA}$	1200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1\text{mA}$	3.5		V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 300$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ Note 2, $T_J = 125^\circ\text{C}$			50 $\mu\text{A}$ 5 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 16A$ , Note 1			340 m $\Omega$

**ISOPLUS i5-Pak™**

 G = Gate      D = Drain  
S = Source

**Features**

- Silicon Chip on Direct-Copper-Bond Substrate
  - High Power Dissipation
  - Isolated Mounting Surface
  - 2500V Electrical Isolation
- Avalanche Rated
- Fast Intrinsic Diode

**Advantages**

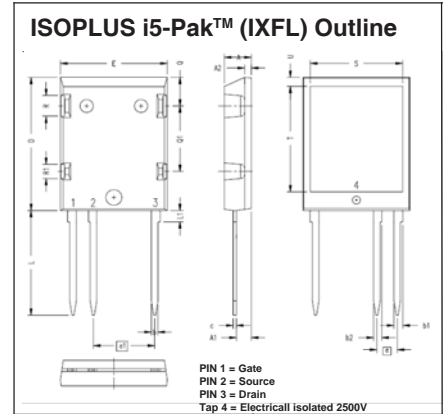
- Easy Assembly
- Space Savings
- High Power Density

**Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}, I_D = 16\text{A}$ , Note 1	17	29	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		21	nF
$C_{oss}$			1105	pF
$C_{rss}$			77	pF
$R_{Gi}$	Gate input resistance		0.84	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 16\text{A}$ $R_G = 1\Omega$ (External)		70	ns
$t_r$			62	ns
$t_{d(off)}$			88	ns
$t_f$			51	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 16\text{A}$		360	nC
$Q_{gs}$			130	nC
$Q_{gd}$			160	nC
$R_{thJC}$			0.24	$^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			32 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			128 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
$Q_{RM}$			1.9	$\mu\text{C}$
$I_{RM}$			15.0	A



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	0.190	0.205	4.83	5.21
A1	0.102	0.118	2.59	3.00
A2	0.046	0.055	1.17	1.40
b	0.045	0.055	1.14	1.40
b1	0.063	0.072	1.60	1.83
b2	0.058	0.068	1.47	1.73
c	0.020	0.029	0.51	0.74
D	1.020	1.040	25.91	26.42
E	0.770	0.799	19.56	20.29
e	0.150 BSC		3.81 BSC	
e1	0.450 BSC		11.43 BSC	
L	0.780	0.820	19.81	20.83
L1	0.080	0.102	2.03	2.59
Q	0.210	0.235	5.33	5.97
Q1	0.490	0.513	12.45	13.03
R	0.150	0.180	3.81	4.57
R1	0.100	0.130	2.54	3.30
S	0.668	0.690	16.97	17.53
T	0.801	0.821	20.34	20.85
U	0.065	0.080	1.65	2.03

**Notes:**

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Part must be heatsunk for high-temp  $I_{CS}$  measurement.

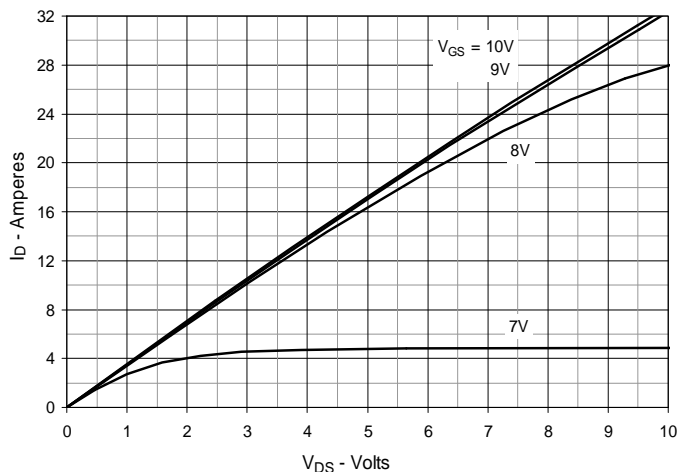
**PRELIMINARY TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

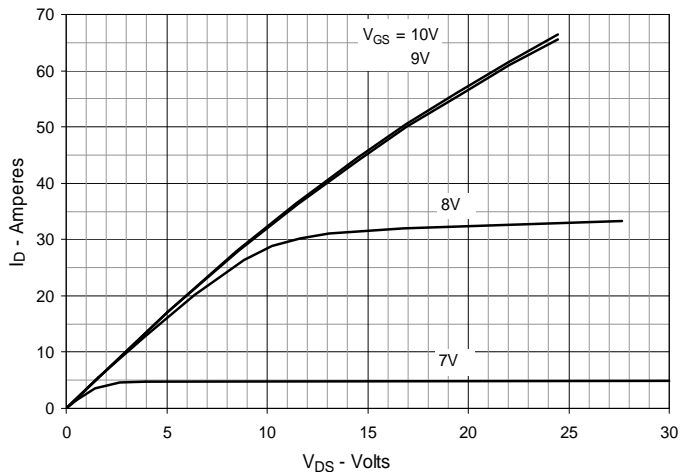
**IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.**

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

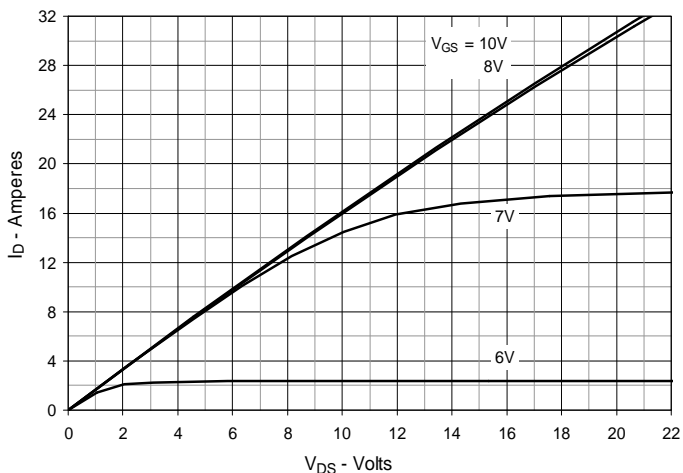
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



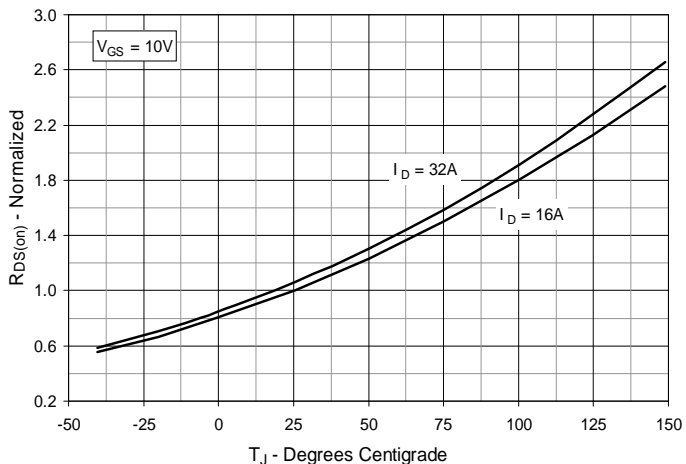
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



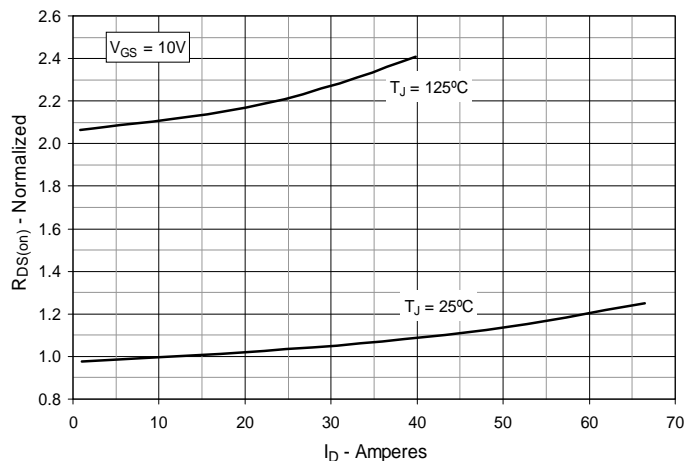
**Fig. 3. Output Characteristics  $T_J = 125^\circ\text{C}$**



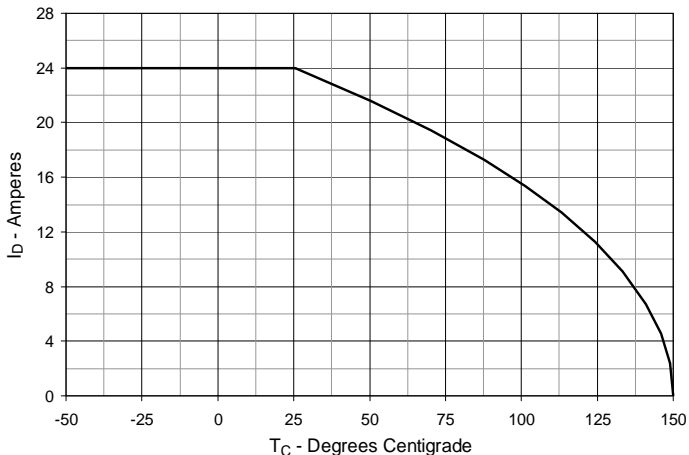
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 16A$  Value vs. Junction Temperature**



**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 16A$  Value vs. Drain Current**



**Fig. 6. Maximum Drain Current vs. Case Temperature**



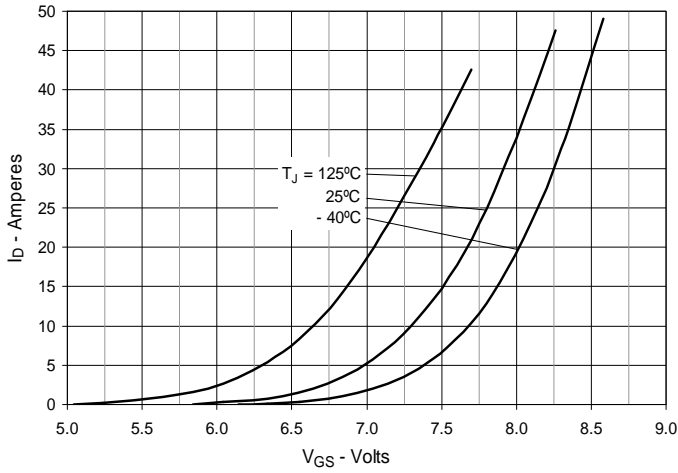
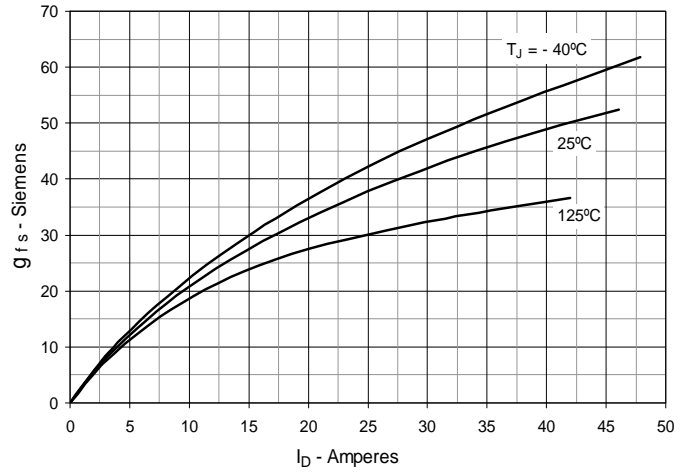
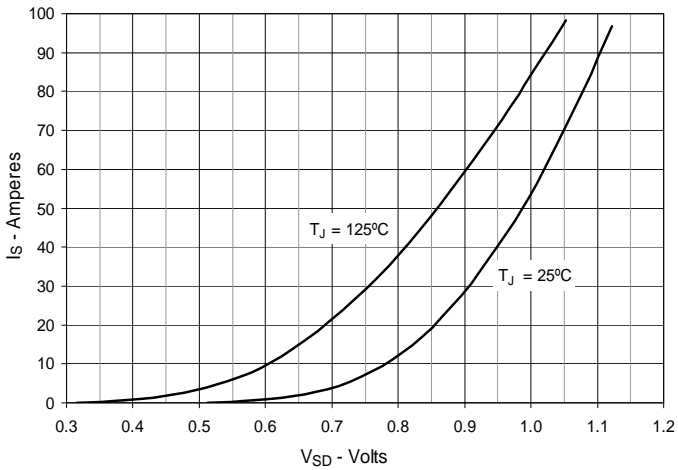
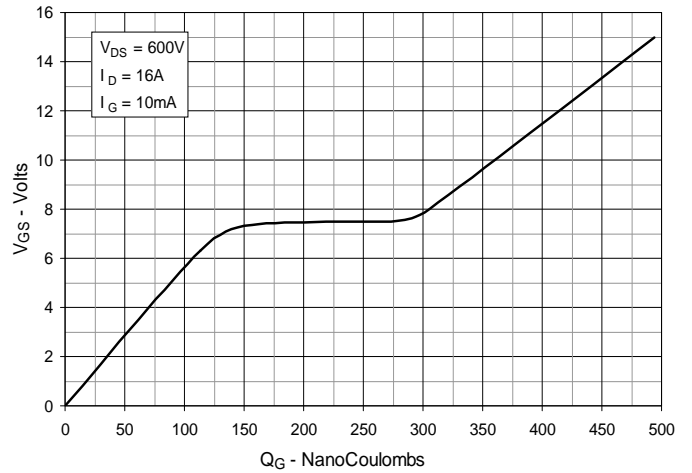
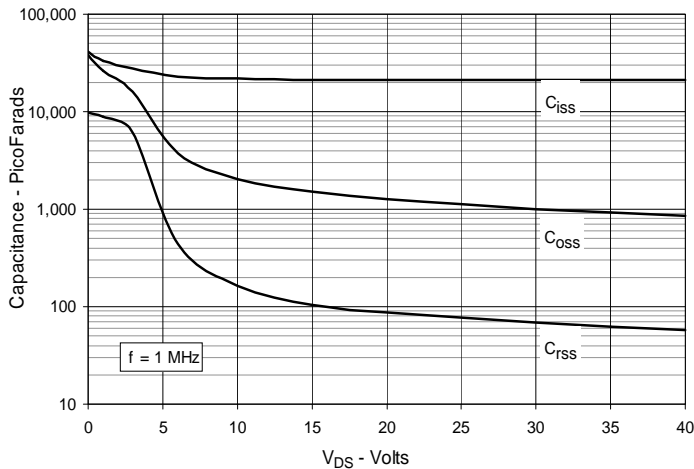
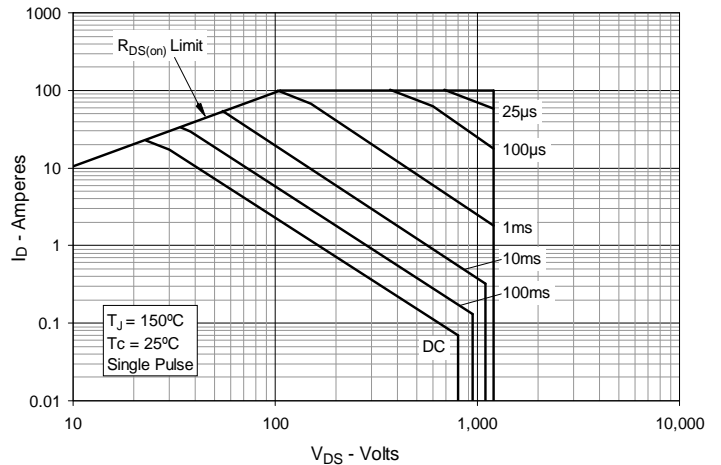
**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Forward-Bias Safe Operating Area**


Fig. 13. Maximum Transient Thermal Impedance

